ROCHESTER INSTITUTE OF TECHNOLOGY MICROELECTRONIC ENGINEERING

Introduction to Electronics

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11-2-2006 Intro_Electronics.ppt

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OUTLINE

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INTRODUCTION

This is a laboratory guide that will introduce the reader to electronic components, ohms's Law, current and voltage measurements and characterization of electronic components.

In addition a brief introduction to digital logic realization is given through the building of simple logic gates and combining these gates to make more complex digital systems.



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DEFINITION OF TERMS

DUT - Device Under Test

Ohm's Law – Fundamental Relationship between current through and voltage across a resistor.

Charge – created by the presence or absence of electrons

Current – movement of charge

Voltage – potential to move charge

Resistor – opposition to the movement of charge

LED – Light Emitting Diode

Diode – device that allows current to flow in one direction only BJT – Bipolar Junction Transistor

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CHARACTERIZATION OF ELECTRONIC DEVICES

Electronic devices are classified by their current-voltage (I-V) characteristics. The I-V characteristics could be measured experimentally or derived theoretically. The experimental approach would involve applying several voltages and measuring the corresponding current. The current vs voltage is plotted and compared with known classifications. For example: a variable voltage supply Vs is used to apply different voltages to the Device Under Test (DUT) while a current meter (I) and Digital Multimeter (DMM) is used to measure I and V



DATA

Data in Table Form I (amps) V (volts) -0.003 -3 -2 -0.002 -0.001 -1 0 0 0.001 1 0.002 2 0.003 3



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DEVICE CLASSIFICATIONS





Resistors have linear I-V characteristics that go through the origin.

Battery has linear I-V characteristics with constant voltage at any current

Diode has exponentially increasing current in the first quadrant and ~ zero current in the third quadrant (until breakdown).



BIPOLAR JUNCTION TRANSISTOR



DIGITAL INTEGRATED CIRCUITS

BOOLEAN ALGEBRA IS BASED ON TWO DISCRETE LEVELSCALLED LOW OR HIGH (0 OR 1).(from George Boole)

BOOLEAN ALGEBRA USES FUNCTIONS SUCH AS "INVERT", "AND", "OR" TO EVALUATE INPUTS AND GENERATE "OUTPUTS".

THE TERM "BINARY LOGIC" IS USED TO DESCRIBE DEVICES THAT FOLLOW THE RULES OF BOOLEAN ALGEBRA.

EACH SUB CIRCUIT OR "GATE" SHOULD HAVE ITS INPUTS AND OUTPUTS AT 0 OR 1 (Except Briefly During Switching)



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INVERTER







MORE LOGIC GATES

3 INPUT AND



3 INPUT OR



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FILP-FLOPS (BASIC MEMORY STORAGE DEVICE)







Q=DATA IF CLOCK IS HIGH IF CLOCK IS LOW Q=PREVIOUS DATA VALUE

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ADDITION IN BINARY

IN BASE 10	0	0000	TRUTH TABLE				
1 0001			FOR ADDITION				
7	2	0010	RULES				
+2	3	0011					
	4	0100	Α	B	CIN	SUM	COUT
9	5	0101	0	0	0	0	0
	6	0110	Ő	0 0	1	1	ů O
IN BINARY	7	0111	Ô	1	0	1	Õ
	8	1000	Ô	1	1	0	1
1 CARRY	9	1001	1	O	0	1	0
111	10	1010	1	Ő	1	0	1
010	11	1011	1	1	0	Ô	1
	12	1100	1	1	1	1	1
1001 SUM	13	1101	_	_	-	_	_
	14	1110					
	15	1111					
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HALF ADDER (EXCLUSIVE OR) XOR

B	Α	NOR	В	A	XOR
0	0	1	0	0	0
0	1	0	0	1	1
1	0	0	1	0	1
1	1	0	1	1	0



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LIST OF LABORATORY MATERIALS

Hook – Up Wire (22 gauge, Solid, PVC colored insulation) Assorted LED's (Qty 6) Solderless Breadboard (2 ¹/₄ " x 6 ¹/₂") Digital Multimeter (AC and DC voltages up to 500V, current up to 200 mA, Resistance up to 2 M ohm) Type 23A battery for Digital Multimeter 9 Volt Alkaline Battery 9 Volt Battery Snap Connectors (Heavy-Duty) 10 K ohm, 15 Turn Cermet Potentiometer (PCB-mount) 1K ohm ¹/₄ watt Resistors (Qty 10) 10K ohm ¹/₄ watt Resistors (Qty 6) NPN BJT Switching Transistors (2N2222 or equivalent) (Qty 6)

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RESISTOR COLOR CODES







VARIABLE VOLTAGE SOURCE

Variable voltage sources (power supply) are commercially available in a wide range of maximum voltage and current values. For this laboratory we can approximate a variable voltage supply using the circuit below.





BUILD AND TEST SIMPLE LOGIC GATES

Build an inverter using resistors and a BJT Build a two input nor gate using resistors and a BJT Build a half adder (XOR)

LED's can be used to test gate outputs



Output high LED on low LED off

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Introduction to Electronics RESISTOR TRANSISTOR REALIZATION OF INVERTER



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RESISTOR TRANSISTOR REALIZATION OF XOR



INTEGRATED CIRCUITS

REFERENCES

- 1. Dr. Fuller's webpage <u>http://www.rit.edu/~lffeee</u>
- 2. more

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REVIEW QUESTIONS

- A 220 ohm resistor has 1.5 volts across it. The current through the resistor is a)1.5 A b) 6.8 mA c) 147 A d)0.068 A
- 2. A diode has minus 1.5 volts across it. The current though the diode is a) infinite b) zero c) $1x10^{-9}$ A d) $-1x10^{-9}$ A
- 3. The I-V characteristics of a constant current source is a linear horizontal line.a) True b) False
- 4. The I-V characteristics of a BJT is a linear line in the first quadrant only a) True b) False
- 5. In resistor-transistor realization of logic gates the purpose of the BJT is toa) act as a voltage controlled switch b) limit the current drawn from the power supply c) provide voltage gain d) provide current gain e) all of the above.

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